

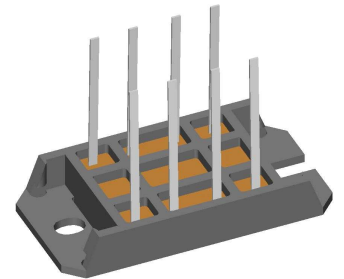
Thyristor Module

3~ Rectifier	
$V_{RRM} =$	1200 V
$I_{DAV} =$	45 A
$I_{FSM} =$	320 A

3~ Rectifier Bridge, half-controlled (high-side)

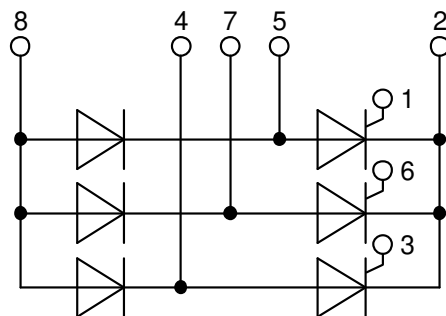
Part number

VVZ40-12io1



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic base plate
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Line rectifying 50/60 Hz
- Drives
- SMPS
- UPS

Package: V1-B-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 10 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

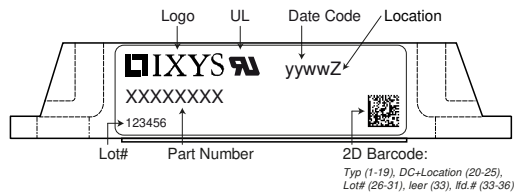
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Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}C$		300	μA
		$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 125^{\circ}C$		5	mA
V_T	forward voltage drop	$I_T = 15\text{ A}$	$T_{VJ} = 25^{\circ}C$		1.12	V
		$I_T = 45\text{ A}$			1.47	V
		$I_T = 15\text{ A}$	$T_{VJ} = 125^{\circ}C$		1.07	V
		$I_T = 45\text{ A}$			1.52	V
I_{DAV}	bridge output current	$T_C = 100^{\circ}C$ rectangular $d = 1/3$	$T_{VJ} = 125^{\circ}C$		45	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}C$		0.85	V
r_T	slope resistance				15	m Ω
R_{thJC}	thermal resistance junction to case				1	K/W
R_{thCH}	thermal resistance case to heatsink			0.6		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		100	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		320	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		345	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}C$		270	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		295	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		510	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		495	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}C$		365	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		360	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}C$		16	pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu s$	$T_C = 125^{\circ}C$		10	W
		$t_p = 300\text{ }\mu s$			1	W
P_{GAV}	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}C; f = 50\text{ Hz}$ repetitive, $I_T = 45\text{ A}$			150	A/ μs
		$t_p = 200\text{ }\mu s; di_G/dt = 0.3\text{ A}/\mu s;$ $I_G = 0.3\text{ A}; V = 2/3 V_{DRM}$ non-repet., $I_T = 15\text{ A}$			500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 125^{\circ}C$		1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}C$		1	V
			$T_{VJ} = -40^{\circ}C$		1.2	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}C$		65	mA
			$T_{VJ} = -40^{\circ}C$		80	mA
V_{GD}	gate non-trigger voltage	$V_D = 2/3 V_{DRM}$	$T_{VJ} = 125^{\circ}C$		0.2	V
I_{GD}	gate non-trigger current				5	mA
I_L	latching current	$t_p = 30\text{ }\mu s$	$T_{VJ} = 25^{\circ}C$		150	mA
		$I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu s$				
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		100	mA
t_{gd}	gate controlled delay time	$V_D = 1/2 V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu s$				
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 15\text{ A}; V = 2/3 V_{DRM}$ $di/dt = 10\text{ A}/\mu s$ $dv/dt = 20\text{ V}/\mu s$ $t_p = 300\text{ }\mu s$	$T_{VJ} = 100^{\circ}C$		150	μs



Package V1-B-Pack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		125	°C
T_{op}	operation temperature		-40		100	°C
T_{stg}	storage temperature		-40		125	°C
Weight				30		g
M_D	mounting torque		2		2.5	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VVZ40-12io1	VVZ40-12io1	Box	5	466352

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 125^{\circ}C$

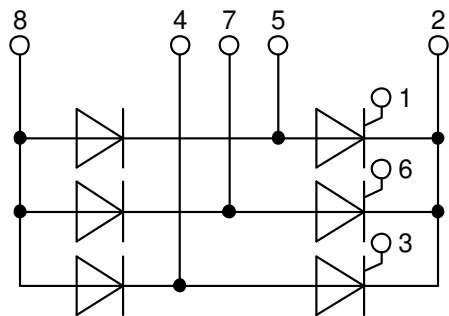
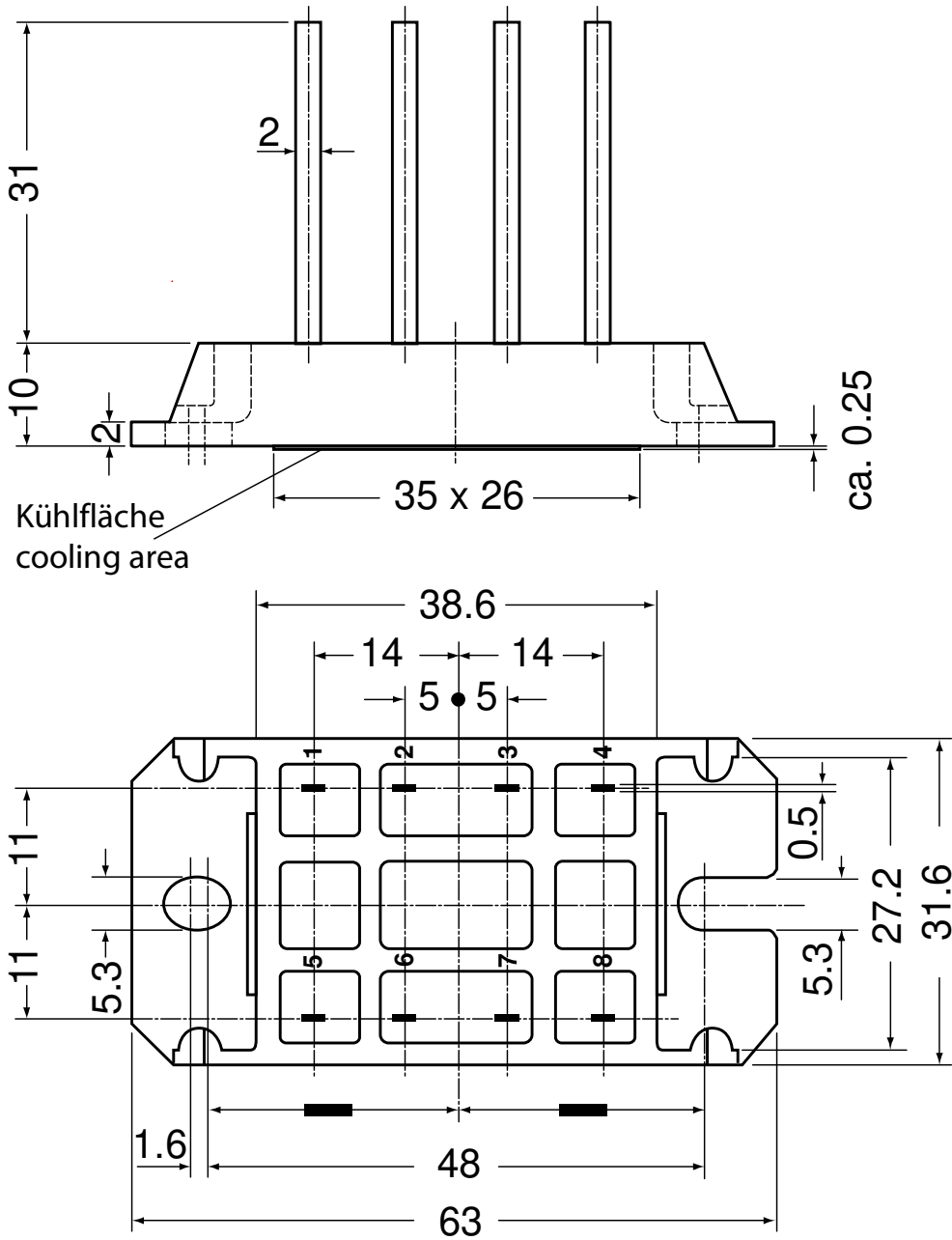


Thyristor

$V_{0\ max}$	threshold voltage	0.85	V
$R_{0\ max}$	slope resistance *	12.5	mΩ



Outlines V1-B-Pack



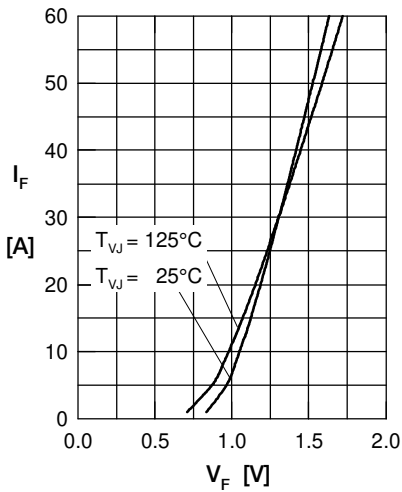
Thyristor


Fig. 1 Forward current vs. voltage drop per thyristor

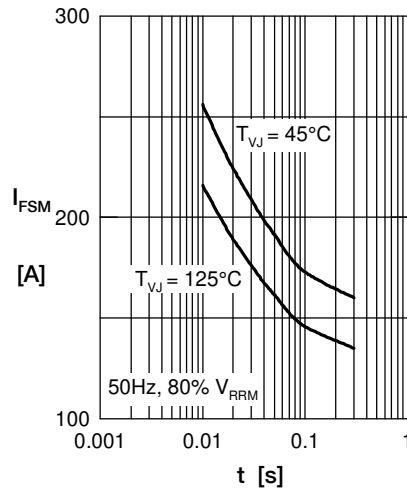


Fig. 2 Surge overload current vs. time per thyristor

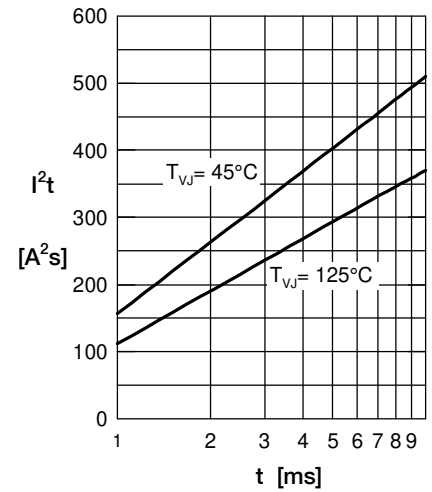
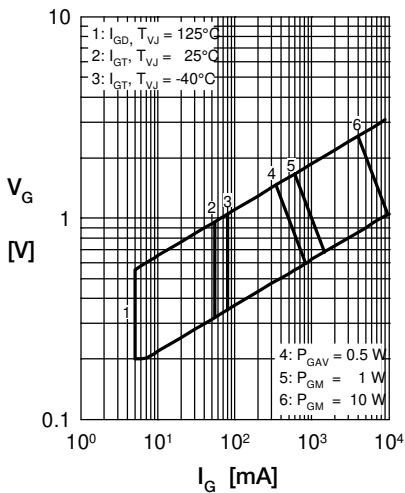

 Fig. 3 I^2t vs. time per thyristor


Fig. 4 Gate trigger characteristics

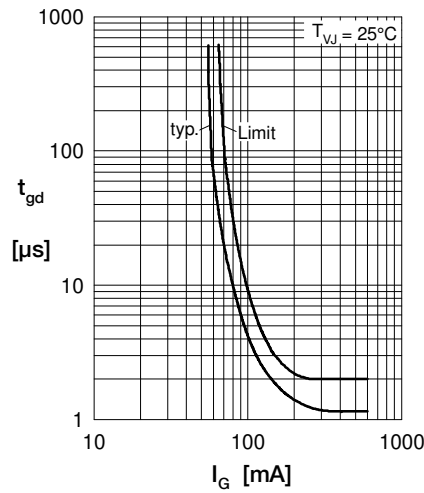


Fig. 5 Gate trigger delay time

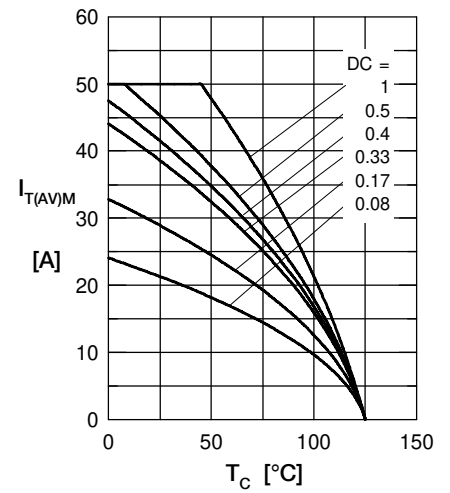


Fig. 5 Max. forward current vs. case temperature per thyristor

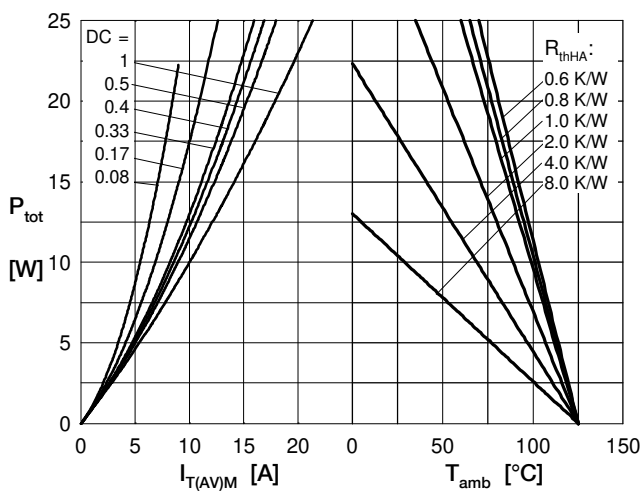


Fig. 4 Power dissipation vs. forward current and ambient temperature per thyristor

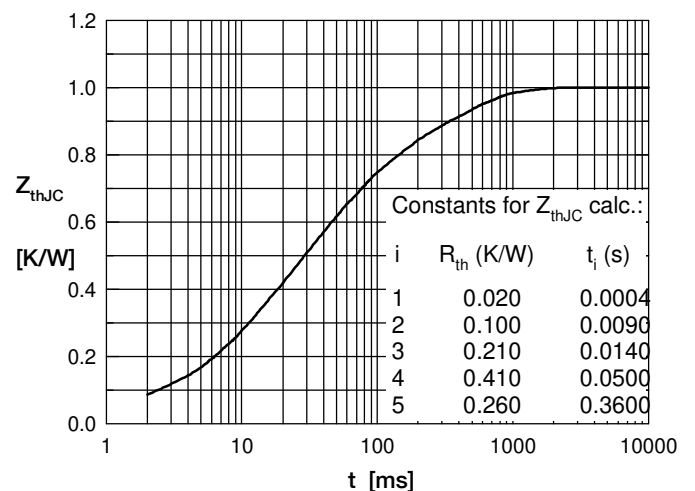


Fig. 6 Transient thermal impedance junction to case vs. time per thyristor